

KSC2335

High Speed, High Voltage Switching

Industrial Use



NPN Epitaxial Silicon Transistor

1.Base 2.Collector 3.Emitter

Absolute Maximum Ratings $\rm T_{C}\text{=}25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	500	V
V _{CEO}	Collector-Emitter Voltage	400	V
V _{EBO}	Emitter-Base Voltage	7	V
I _C	Collector Current (DC)	7	Α
I _{CP}	*Collector Current (Pulse)	15	A
I _B	Base Current (DC)	3.5	Α
P _C	Collector Dissipation (T _a =25°C)	1.5	W
P _C	Collector Dissipation (T _C =25°C)	40	W
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	- 55 ~ 150	°C

^{*} PW≤300μs, Duty Cycle≤10%

Electrical Characteristics $\rm T_{C}{=}25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
V _{CEO} (sus)	Collector-Emitter Sustaining Voltage	I _C = 3A, I _{B1} = 0.6A, L = 1mH	400		V
V _{CEX} (sus)1	Collector-Emitter Sustaining Voltage	$I_C = 3A$, $I_{B1} = -I_{B2} = 0.6A$ $V_{BE}(off) = -5V$, $L = 180\mu H$, Clamped	450		V
V _{CEX} (sus)2	Collector-Emitter Sustaining Voltage	$I_C = 6A, I_{B1} = 2A, I_{B2} = -0.6A$ $V_{BE}(off) = -5V, L = 180\mu H, Clamped$	400		V
I _{CBO}	Collector Cut-off Current	$V_{CB} = 400V, I_{E} = 0$		10	μΑ
I _{CER}	Collector Cut-off Current	$V_{CE} = 400V, R_{BE} = 51\Omega @ T_{C} = 125^{\circ}C$		1	mA
I _{CEX1}	Collector Cut-off Current	V _{CE} = 400V, V _{BE} (off)= -1.5V		10	μΑ
I _{CEX2}	Collector Cut-off Current	$V_{CE} = 400V, V_{BE}(off) = -1.5V @ T_{C} = 125^{\circ}C$		1	mA
I _{EBO}	Emitter Cut-off Current	$V_{EB} = 5V, I_{C} = 0$		10	μΑ
h _{FE1} h _{FE2} h _{FE3}	* DC Current Gain	$V_{CE} = 5V, I_{C} = 0.1A$ $V_{CE} = 5V, I_{C} = 1A$ $V_{CE} = 5V, I_{C} = 3A$	20 20 10	80 80	
V _{CE} (sat)	* Collector-Emitter Saturation Voltage	$I_C = 3A, I_B = 0.6A$		1	V
V _{BE} (sat)	* Base-Emitter Saturation Voltage	I _C = 3A, I _B = 0.6A		1.2	V
t _{ON}	Turn ON Time	V _{CC} =150V, I _C = 3A		1	μs
t _{STG}	Storage Time	$I_{B1} = -I_{B2} = 0.6A$		2.5	μs
t _F	Fall Time	$R_L = 50\Omega$		1	μs

^{*} Pulse Test: PW≤350μs, Duty Cycle≤2% Pulsed

h_{FE} Classification

Classification	R	0	Υ
h _{FE2}	20 ~ 40	30 ~ 60	40 ~ 80

Typical Characteristics

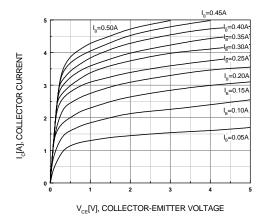


Figure 1. Static Characteristic

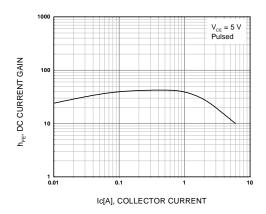


Figure 2. DC current Gain

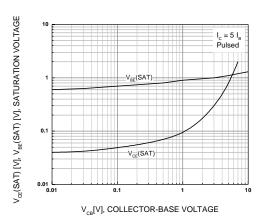


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

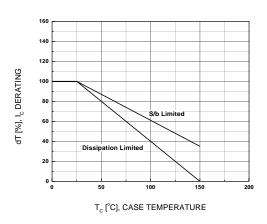


Figure 4. Derating Curve of Safe Operating Areas

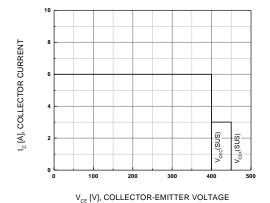


Figure 5. Reverse Bias Safe Operating Area

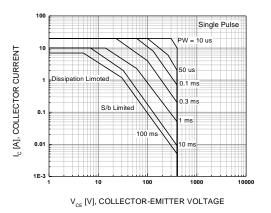
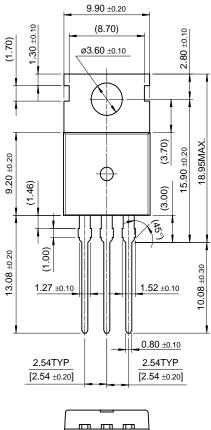


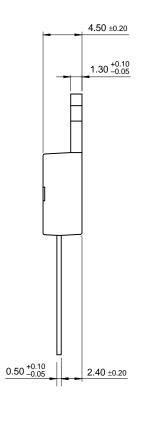
Figure 6. Forward Bias Safe Operating Area

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Package Demensions

TO-220





10.00 ±0.20

Dimensions in Millimeters

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